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U.S. Patent Documents

Examiner	DOCUMENT NUMBER	DATE	Name	CLASS	SUB	FILING DATE
Initial					CLASS	
	2007/0128470	6/7/2007	Nagahama et al.		_	2/12/2007
	2004/0144995	7/29/2004	Nagahama et al.			5/24/2002
	2004/0245553	12/9/2004	Hosomi et al.			4/8/2003
	2006/0056115	3/16/2006	Djayaprawira et al.			9/7/2005

Foreign Patent Documents

Examiner	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLA	Sub-	Translation	
Initial				ss	CLASS	YES	No
	2003-318465*	4/23/2002	Japan			Abstract	
	WO 2002/099905	5/24/2002	PCT			Abstract	
	EP 1 391 942	5/24/2002	EP			X	
	2002-204004	12/28/2000	Japan			Abstract	X
	2002-289943	3/26/2001	Japan			Abstract	X
	2003-304010**	4/9/2002	Japan			Abstract	
	WO 2003/085750	4/8/2003	PCT			Abstract	
	EP 1 494 295 .	4/8/2003	EP			X	
	2006-080116***	9/7/2004	Japan			Abstract	

- * Corresponds to U.S. Patent 2007/0128470, U.S. Patent 2004/0144995, WO2002/099905, and EPI 391 942, listed above.
- ** Corresponds to U.S. Patent 2004/0245553, WO 2003/085750, and EP 1 494 295, listed above.
- *** Corresponds to U.S. Patent 2006/0056115, listed above.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /AC/ (10/26/2009)

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Other Documents (Including Author, Title, Date Pertinent Pages, Etc.) Wolf, S.A. et al., "Spintronics: A Spin-Based Electronics Vision for the Future", Science, Vol. 294, November 16, 2001, pp. 1488-1495. Wulfhekel, W. et al., "Single-Crystal Magnetotunnel Junctions", Applied Physics Letters, Vol. 78, No. 4, January 22, 2001, pp. 509-511 Julliere, M., "Tunneling Between Ferromagnetic Films", Physics Letters, Vol. 54A, No. 3, September 8, 1975, pp.225-226. Soulen, R.J.., Jr. et al., "Measuring the Spin Polarization of a Metal with a Superconducting Point Contact", Science, Vol. 282, October 2, 1998, pp. 85-88. Saito, Y. et al., "Correlation between Barrier Width, Barrier Height, and DC Bias Voltage Dependences on the Magnetoresistance Ratio in Ir-Mn Exchange Biased Single and Double Tunnel Junctions", Jpn. J. Appl. Phys., Vol. 39 (2000), pp. L1035-L1-38. lura, S. et al., "Enhancement of Thermal Stability in Ferromagnetic Tunnel Junctions Prepared by the Radical Oxidation Method", Journal of the Magnetics Society of Japan, Vol. 26, No. 6 (2002), pp. 839-842, abstract only in English. Bowen, M. et al., "Large Magnetoresistance in Fe/MgO/FeCo(001) Epitaxial Tunnel Junctions on GaAs(001)", Applied Physics Letters, Vol. 79, No. 11, September 10, 2001, pp. 1655-1657. Simmons, John G., "Generalized Formula for the Electric Tunnel Effect between Similar Electrodes Separated by a Thin Insulating Film", Journal of Applied Physics, Vol. 34, NO. 6, June 1963, pp. 1793-1803. Vassent, J.L. et al., "A Study of Growth and the Relaxation of Elastic Strain in MgO on Fe(001)", J. Appl. Phys. Vol. 80, No. 10, November 15, 1996, pp. 5727-5735. Faure-Vincent, J. et al., "High Tunnel Magnetoresistance in Expitaxial Fe/MgO/Fe Tunnel Junctions", Applied Physics Letters, Vol. 82, No. 25, June 23, 2003, pp. 4507-4509. Meyerheim, H.L. et al., "Geometrical and Compositional Structure at Metal-Oxide Interfaces: MgO on Fe(001)", Physical Review Letters, Vol. 18, No. 7, August 13, 2001, pp. 076102-1 - 076102-4. Butler, W.H. et al., "Spin-dependent Tunneling Conductance of Fe[MgO]Fe Sandwiches", Physical Review B., Vol. 63, 054416, 2001, pp. 054416-1 - 054416-12. Mathon, J. et al., "Theory of Tunneling Magnetoresistance of an Epitaxial Fe/MgO/Fe(001) Junction", Physical Review B., Vol. 63, 220403(R), 2001, pp. 220403-1 - 220403-4. Zhang, X.-G. et al., "Effects of the Iron-Oxide Layer in Fe-FeO-MgO-Fe Tunneling Junctions", Physical Review B, Vol. 68, 092402, 2003, pp. 092402-1 - 092402-4. Zhang, X.-G. et al., "Large Magnetoresistance in bcc Co/MgO/Co and FeCo/MgO/FeCo Tunnel Junctions", Physical Review B., Vol. 70, 172407, 2004, pp. 172407-1 - 172407-4. Gibson, A. et al., "Stability of Vacancy Defects in MgO: The Role of Charge Neutrality", Physical Review B., Vol. 50, No. 4, July 15, 1994-II, pp. 2582-2592. Yuasa, S. et al., "High Tunnel Magnetoresistance at Room Temperature in Fully Expitaxial Fe/MgO/Fe Tunnel Junctions Due to Coherent Spin-Polarized Tunneling", Japanese Journal of Applied Physics, Vol. 43, No. 4B, 2004, pp. L588-L590. /Alonzo Chambliss/ (10/26/2009) DATE CONSIDERED EXAMINER

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